WHAT IS CLAIMED IS:

1. A semiconductor device, comprising:

a stack structure including interlayer insulating layers and electrode patterns which are alternately stacked on each other; and

a support passing through the stack structure,

wherein each of the electrode patterns includes a first conductive pattern, penetrated by the support, at least one second conductive pattern, extending along a side portion of the stack structure, and at least one third conductive pattern disposed between the first conductive pattern and the support, and

wherein the first conductive pattern includes a first conductive material and each of the second and third conductive patterns includes a second conductive material having a lower resistance than the first conductive material.

2. The semiconductor device of claim 1, wherein the first conductive pattern extends between the second conductive pattern and the third conductive pattern.

3. The semiconductor device of claim 1, wherein the second conductive pattern is coupled to the third conductive

pattern.

4. The semiconductor device of claim 1, further comprising channel structures passing through the stack structure.

5. The semiconductor device of claim 1, wherein the support includes protrusions protruding towards both sides of the stack structure to form a T-shape.

6. The semiconductor device of claim 5, wherein the third conductive pattern extends along a sidewall of at least one of the protrusions.